Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

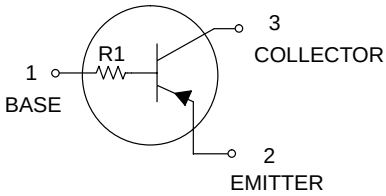
LDTA113TLT1G

- **Applications**
  Inverter, Interface, Driver

- **Features**
  1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see equivalent circuit).
  2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input. They also have the advantage of almost completely eliminating parasitic effects.
  3) Only the on/off conditions need to be set for operation, making the device design easy.

- We declare that the material of product compliance with RoHS requirements.

SOT–23



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	−50	V
Collector-emitter voltage	V_{CEO}	−50	V
Emitter-base voltage	V_{EBO}	−5 to +10	V
Collector current	I_C	−100	mA
Collector Power dissipation	Pc	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA113TLT1G	O2	1	–	3000/Tape & Reel
LDTA113TLT3G	O2	1	–	10000/Tape & Reel

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	–50	–	–	V	I_C= –50μA
Collector-emitter breakdown voltage	BV_{CEO}	–50	–	–	V	I_C= –1mA
Emitter-base breakdown voltage	BV_{EBO}	–5	–	–	V	I_E= –50μA
Collector cutoff current	I_{CBO}	–	–	–0.5	μA	V_{CB}= –50V
Emitter cutoff current	I_{EBO}	–	–	–0.5	μA	V_{EB}= –4V
Collector-emitter saturation voltage	$V_{CE(sat)}$	–	–	–0.3	V	I_C/I_B= –5mA / –0.25mA
DC current transfer ratio	h_{FE}	100	250	600	–	I_C= –1mA , V_{CE}= –5V
Input resistance	R_1	0.7	1	1.3	kΩ	–
Transition frequency	f_T *	–	250	–	MHz	V_{CB}= –10V , I_E=5mA , f=100MHz

* Characteristics of built-in transistor

LDTA113TLT1G

●Electrical characteristic curves

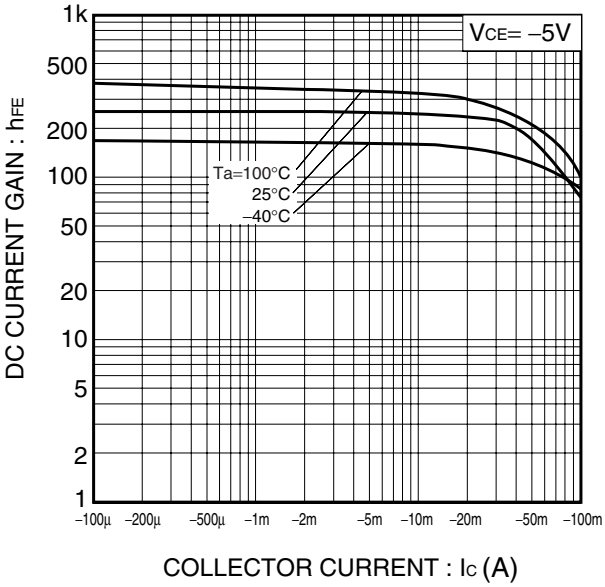


Fig.1 DC Current gain vs. Collector Current

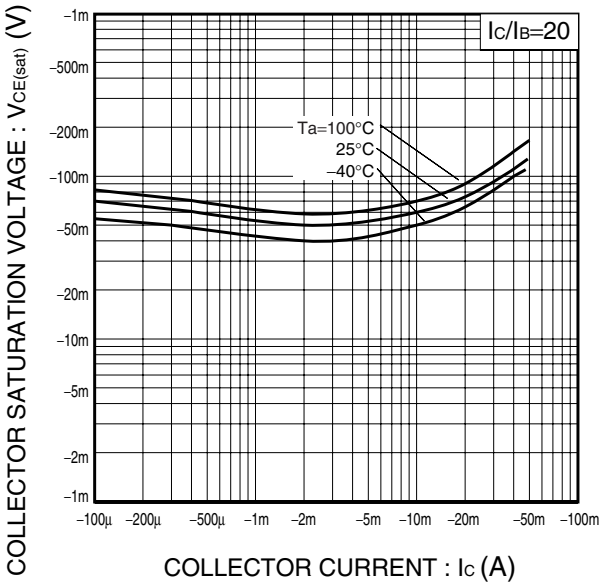
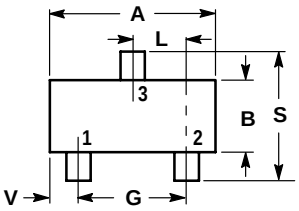
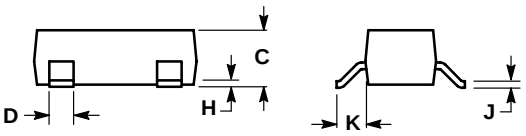


Fig.2 Collector-emitter saturation voltage vs. Collector Current

LDTA113TLT1G

SOT–23





NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M,1982
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60